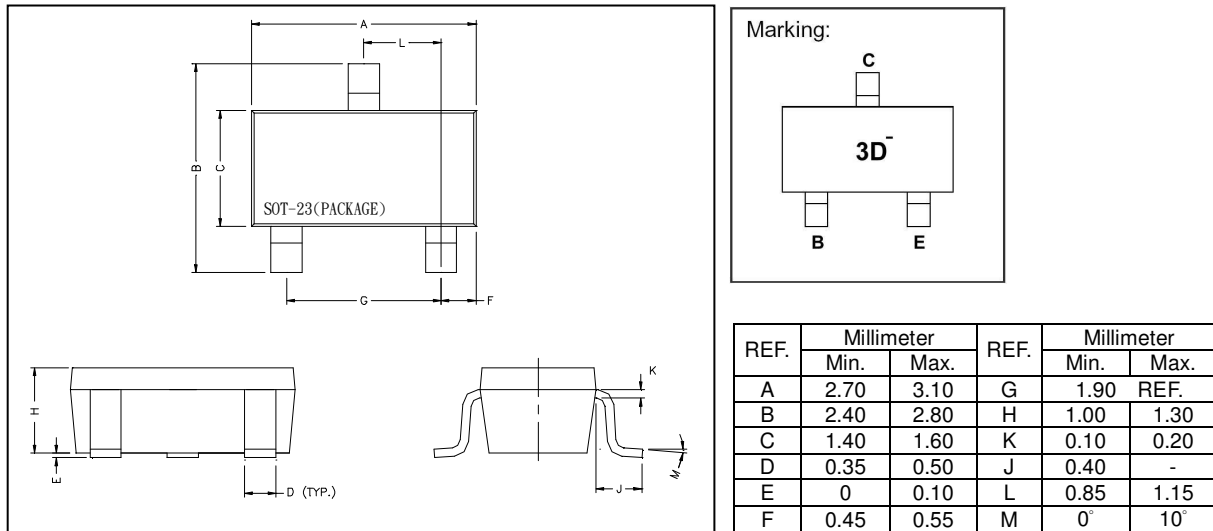


GMBTA44**NPN EPITAXIAL PLANAR TRANSISTOR****Description**

The GMBTA44 is designed for application requires high voltage.

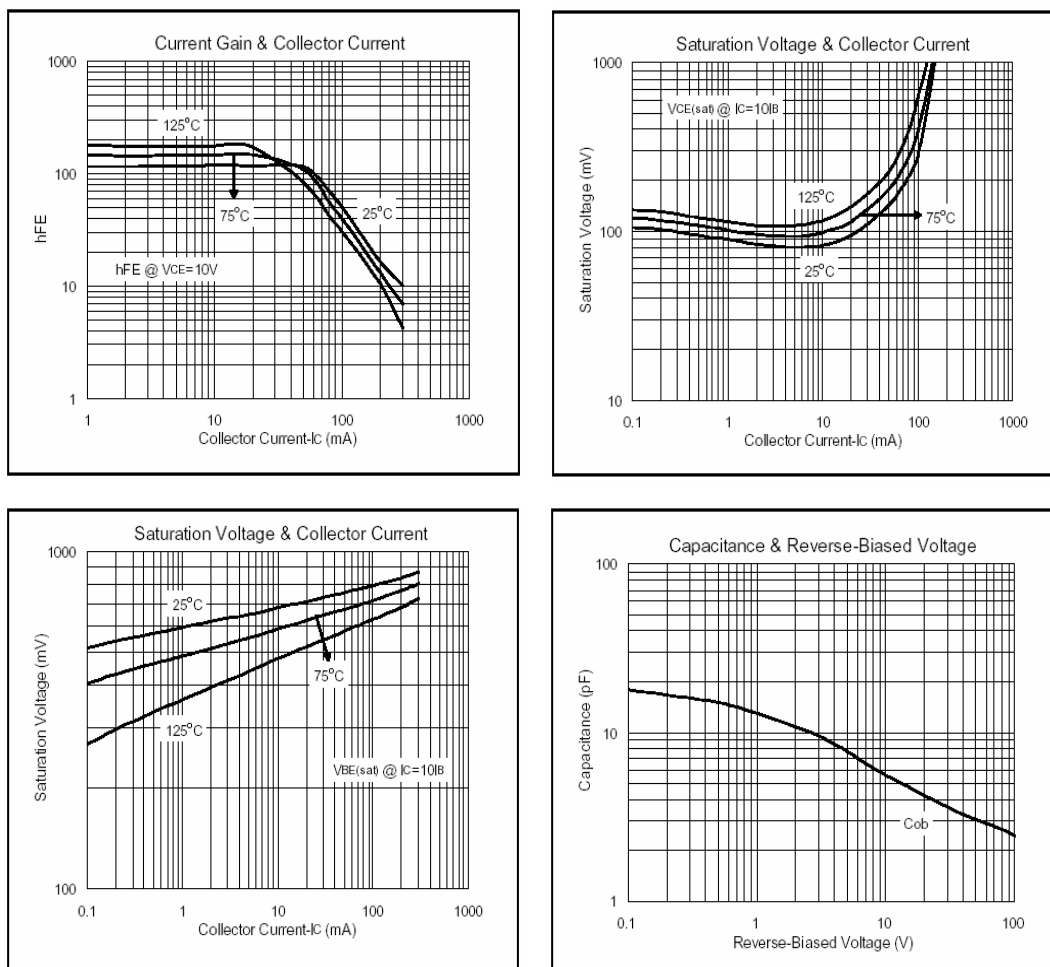
Package Dimensions**Absolute Maximum Ratings at Ta = 25°C**

Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+150	°C
Storage Temperature	Tstg	-55~+150	°C
Collector to Base Voltage	Vcbo	500	V
Collector to Emitter Voltage	Vceo	400	V
Emitter to Base Voltage	Vebo	6	V
Collector Current	Ic	300	mA
Total Power Dissipation	PD	350	mW

Electrical Characteristics (Ta = 25°C, unless otherwise noted)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVcbo	500	-	-	V	Ic=100uA, IE=0
BVceo	400	-	-	V	Ic=1mA, IB=0
BVebo	6	-	-	V	IE=10uA, Ic=0
Icbo	-	-	100	nA	Vcb=400V, IE=0
IEBO	-	-	100	nA	VEB=4V, Ic=0
ICES	-	-	500	nA	Vce=400V
VCE(sat)1	-	-	375	mV	Ic=20mA, IB=2mA
VCE(sat)2	-	-	750	mV	Ic=50mA, IB=5mA
VBE(sat)	-	-	750	mV	Ic=10mA, IB=1mA
hFE1	40	-	-		VCE=10V, Ic=1mA
hFE2	40	-	300		VCE=10V, Ic=10mA
hFE3	45	-	-		VCE=10V, Ic=50mA
hFE4	20	-	-		VCE=10V, Ic=100mA
Cob	-	4	6	pF	Vcb=20V, f=1MHz

Characteristics Curve

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Head Office And Factory:

- **Taiwan:** No. 17-1 Tatung Rd. Fu Kou Hsin-Chu Industrial Park, Hsin-Chu, Taiwan, R. O. C.
TEL : 886-3-597-7061 FAX : 886-3-597-9220, 597-0785
- **China:** (201203) No.255, Jang-Jiang Tsai-Lueng RD. , Pu-Dung-Hsin District, Shang-Hai City, China
TEL : 86-21-5895-7671 ~ 4 FAX : 86-21-38950165